

METHOD AND STRUCTURE FOR INTEGRATED THERMISTOR

Abstract

A structure and method are provided for forming a thermistor. Isolation structures are formed in a substrate including at least an upper layer of a single crystal semiconductor. A layer of salicide precursor is deposited over the isolation region and the upper layer. The salicide precursor is then reacted with the upper layer to form a salicide self-aligned to the upper layer. Finally, the unreacted portions of the salicide precursor are then removed while preserving a portion of the salicide precursor over the isolation region as a body of the thermistor. An alternative integrated circuit thermistor is formed from a region of thermistor material in an embossed region of an interlevel dielectric (ILD).